Application No.: 09/976,342 Docket No.: EMCORE 3.0-047

IN THE SPECIFICATION

In the Title:

Please amend the title to read:

--METHOD OF MAKING AN ALIGNED ELECTRODE ON A SEMICONDUCTOR STRUCTURE--.

In the Abstract:

A method of making a transparent electrode for a light-emitting diode includes depositing metal on a top surface of a semiconductor structure, and defining a first region of the semiconductor structure for a first electrode by forming a mask over the metal, the mask having at least one opening so that the first region is covered by the mask and a second region is aligned with the at least one opening in the mask. The method also includes removing metal aligned with the at least one opening in the mask in the second region to form the first electrode overlying the first region of the semiconductor structure and so as to reveal the top surface semiconductor structure in the second region. After forming the first electrode during the removing metal step, material is removed from the semiconductor structure aligned with the at least one opening in the second region to form a electrode surface for a second electrode, the second electrode surface being lower in elevation than the top surface of the semiconductor structure.